

Complementary 30 V (G-S) MOSFET

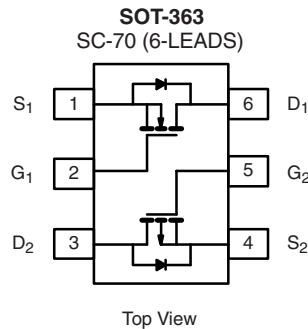
PRODUCT SUMMARY			
	V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A)
N-Channel	30	0.480 at V _{GS} = 10 V	0.63
		0.700 at V _{GS} = 4.5 V	0.52
P-Channel	- 30	0.940 at V _{GS} = - 10 V	- 0.45
		1.700 at V _{GS} = - 4.5 V	- 0.33

FEATURES

- TrenchFET[®] Power MOSFET
- Material categorization:
For definitions of compliance please see www.vishay.com/doc?99912



RoHS
COMPLIANT
HALOGEN
FREE
Available



Marking Code



Ordering Information: Si1539DL-T1-E3 (Lead (Pb)-free)
Si1539DL-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)							
Parameter	Symbol	N-Channel		P-Channel		Unit	
		5 s	Steady State	5 s	Steady State		
Drain-Source Voltage	V _{DS}	30		- 30		V	
Gate-Source Voltage	V _{GS}	± 20					
Continuous Drain Current (T _J = 150 °C) ^a	I _D	T _A = 25 °C	0.63	0.54	- 0.45	- 0.42	A
		T _A = 85 °C	0.45	0.43	- 0.32	- 0.31	
Pulsed Drain Current	I _{DM}	1					
Continuous Source Current (Diode Conduction) ^a	I _S	0.25	0.23	- 0.25	- 0.23	W	
Maximum Power Dissipation ^a	P _D	T _A = 25 °C	0.30	0.27	0.30		0.27
		T _A = 85 °C	0.16	0.14	0.16	0.14	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150				°C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	t ≤ 5 s	R _{thJA}	360	415	°C/W
	Steady State		400	460	
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	300	350	

Notes:

a. Surface mounted on 1" x 1" FR4 board.

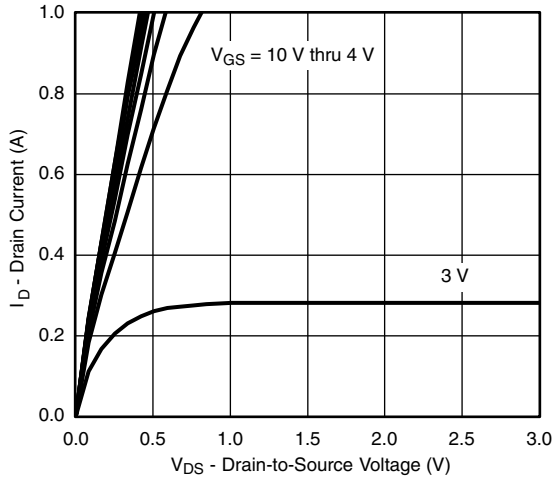
SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)							
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit	
Static							
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	N-Ch	1		2.6	V
		$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	P-Ch	-1		-2.6	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$	N-Ch			± 100	nA
			P-Ch			± 100	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 24\text{ V}, V_{GS} = 0\text{ V}$ $V_{DS} = -24\text{ V}, V_{GS} = 0\text{ V}$ $V_{DS} = 24\text{ V}, V_{GS} = 0\text{ V}, T_J = 85\text{ }^\circ\text{C}$ $V_{DS} = -24\text{ V}, V_{GS} = 0\text{ V}, T_J = 85\text{ }^\circ\text{C}$	N-Ch			1	μA
			P-Ch			-1	
			N-Ch			5	
			P-Ch			-5	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}, V_{GS} = 10\text{ V}$ $V_{DS} \leq -5\text{ V}, V_{GS} = -10\text{ V}$	N-Ch	1			A
			P-Ch	-1			
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 0.59\text{ A}$ $V_{GS} = -10\text{ V}, I_D = -0.42\text{ A}$ $V_{GS} = 4.5\text{ V}, I_D = 0.2\text{ A}$ $V_{GS} = -4.5\text{ V}, I_D = -0.2\text{ A}$	N-Ch		0.410	0.480	Ω
			P-Ch		0.800	0.940	
			N-Ch		0.600	0.700	
			P-Ch		1.500	1.700	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 15\text{ V}, I_D = 0.59\text{ A}$ $V_{DS} = -15\text{ V}, I_D = -0.42\text{ A}$	N-Ch		0.75		S
			P-Ch		0.5		
Diode Forward Voltage ^a	V_{SD}	$I_S = 0.23\text{ A}, V_{GS} = 0\text{ V}$ $I_S = -0.23\text{ A}, V_{GS} = 0\text{ V}$	N-Ch		0.80	1.2	V
			P-Ch		-0.86	-1.2	
Dynamic^b							
Total Gate Charge	Q_g	N-Channel $V_{DS} = 15\text{ V}, V_{GS} = 10\text{ V}, I_D = 0.59\text{ A}$	N-Ch		0.86	1.4	nC
Gate-Source Charge	Q_{gs}		P-Ch		0.90	1.4	
Gate-Drain Charge	Q_{gd}	P-Channel $V_{DS} = -15\text{ V}, V_{GS} = -10\text{ V}, I_D = -0.42\text{ A}$	N-Ch		0.24		
			P-Ch		0.21		
Turn-On Delay Time	$t_{d(on)}$	N-Channel $V_{DD} = 15\text{ V}, R_L = 30\text{ }\Omega$ $I_D \cong 0.5\text{ A}, V_{GEN} = 10\text{ V}, R_g = 6\text{ }\Omega$	N-Ch		5	10	ns
			P-Ch		4	10	
Rise Time	t_r	P-Channel $V_{DD} = -15\text{ V}, R_L = 30\text{ }\Omega$ $I_D \cong -0.5\text{ A}, V_{GEN} = -10\text{ V}, R_g = 6\text{ }\Omega$	N-Ch		8	15	
			P-Ch		8	15	
Turn-Off Delay Time	$t_{d(off)}$	N-Channel $V_{DD} = 15\text{ V}, R_L = 30\text{ }\Omega$ $I_D \cong 0.5\text{ A}, V_{GEN} = 10\text{ V}, R_g = 6\text{ }\Omega$	N-Ch		8	15	
			P-Ch		5	10	
Fall Time	t_f	P-Channel $V_{DD} = -15\text{ V}, R_L = 30\text{ }\Omega$ $I_D \cong -0.5\text{ A}, V_{GEN} = -10\text{ V}, R_g = 6\text{ }\Omega$	N-Ch		7	15	
			P-Ch		7	15	
Source-Drain Reverse Recovery Time	t_{rr}	$I_F = 0.23\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$ $I_F = -0.23\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$	N-Ch		15	30	
			P-Ch		20	40	

Notes:

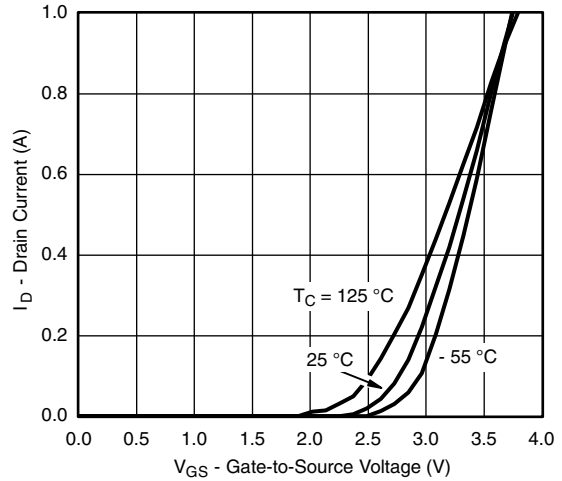
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

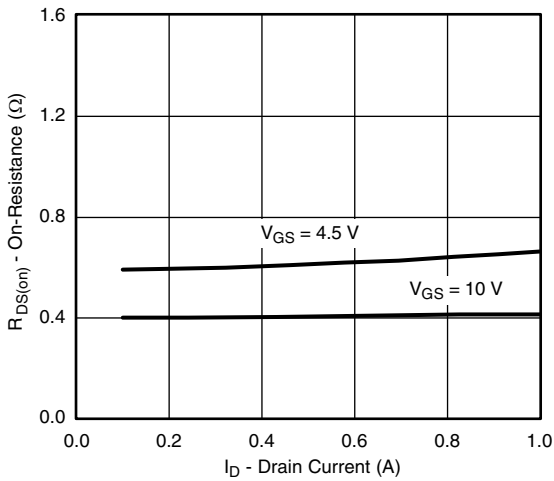
N-CHANNEL TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



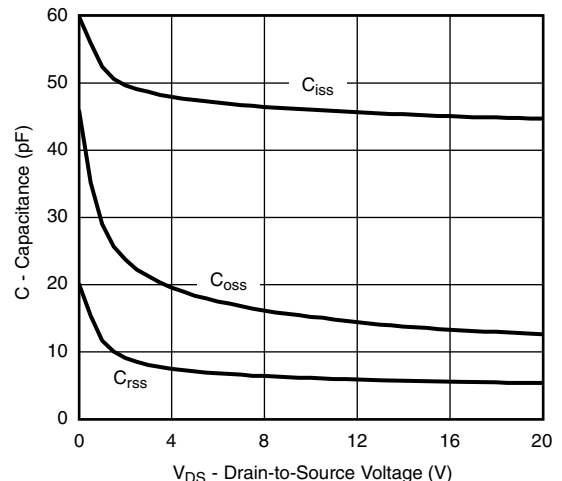
Output Characteristics



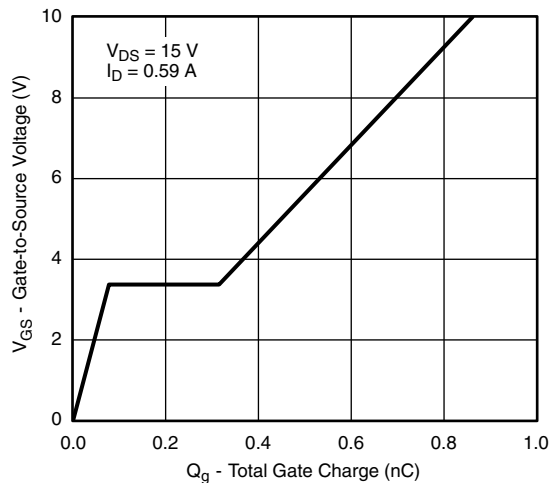
Transfer Characteristics



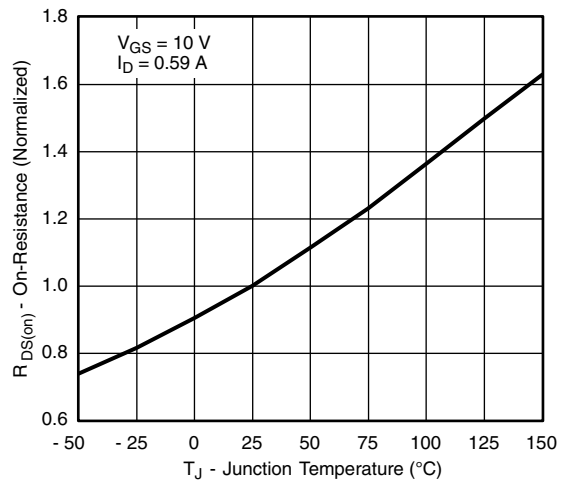
On-Resistance vs. Drain Current



Capacitance

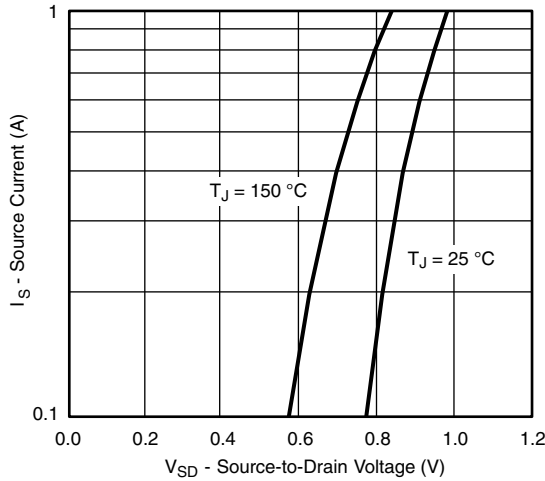


Gate Charge

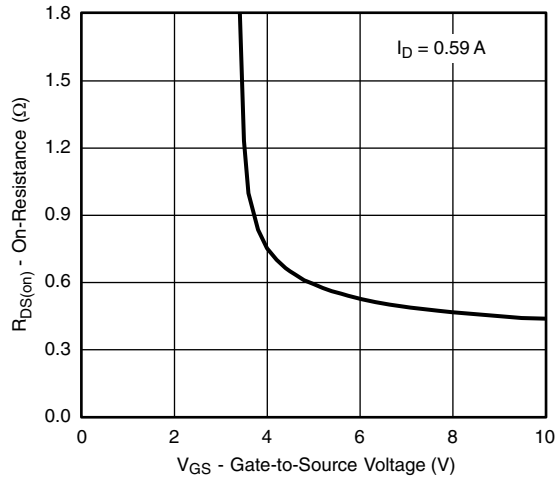


On-Resistance vs. Junction Temperature

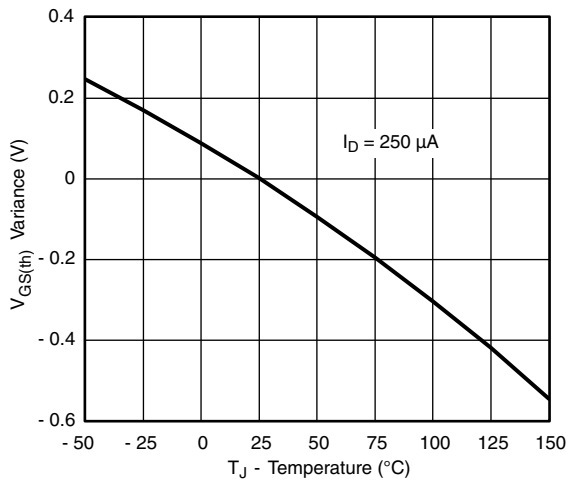
N-CHANNEL TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



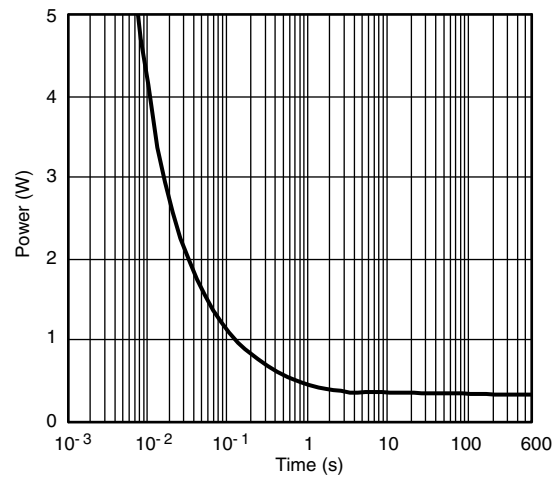
Source-Drain Diode Forward Voltage



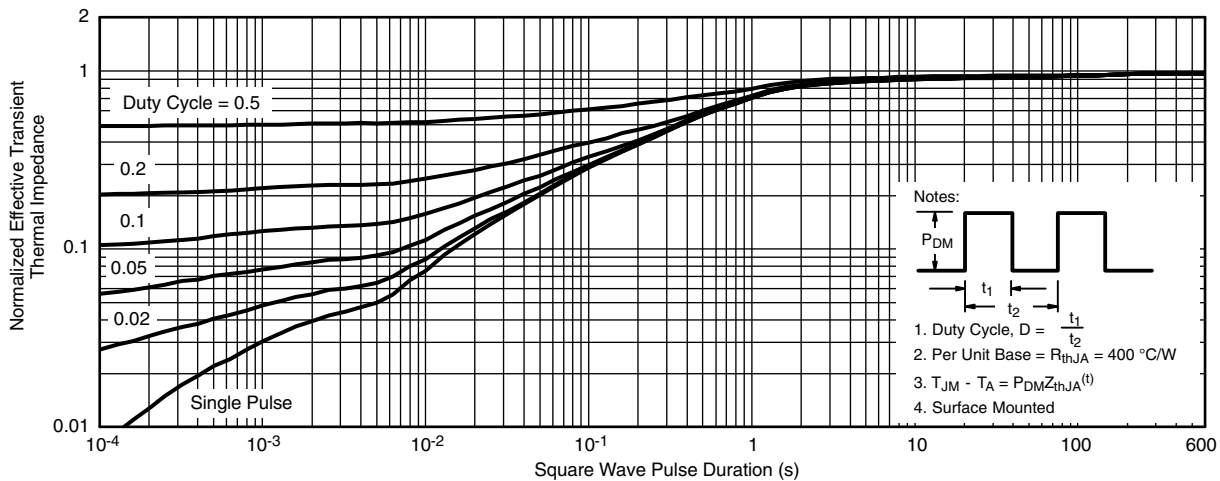
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage

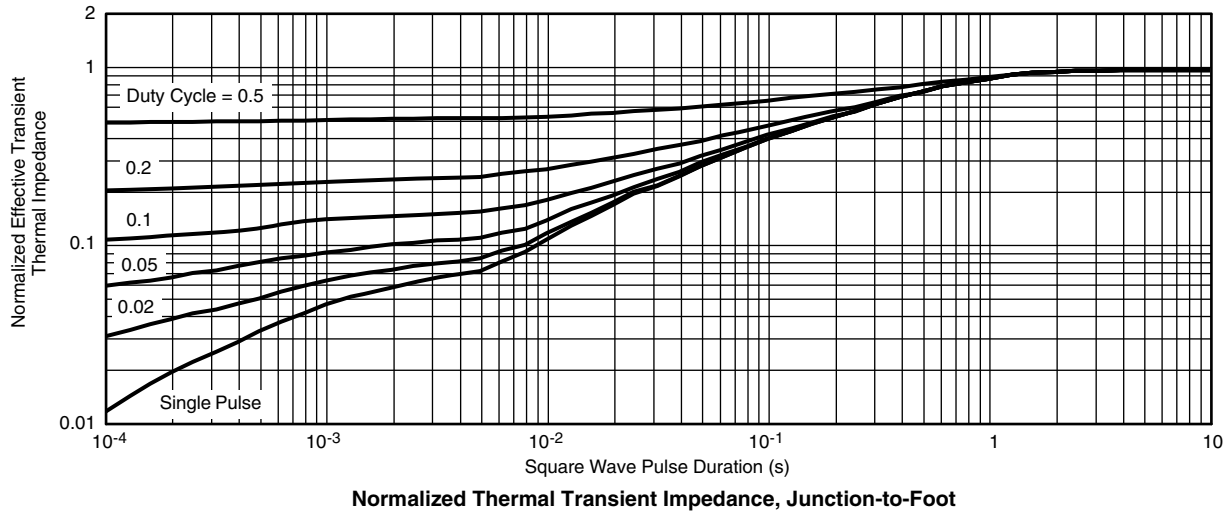


Single Pulse Power

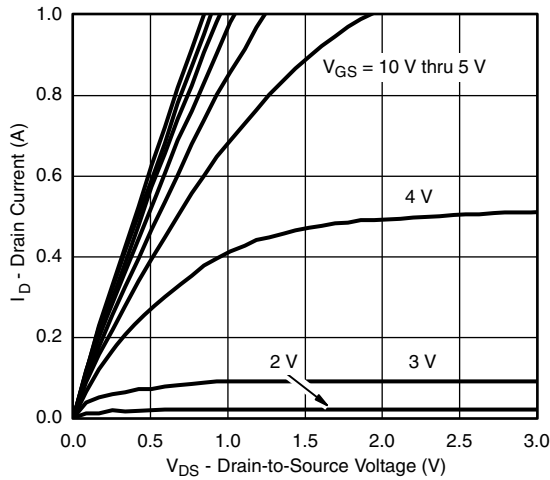


Normalized Thermal Transient Impedance, Junction-to-Ambient

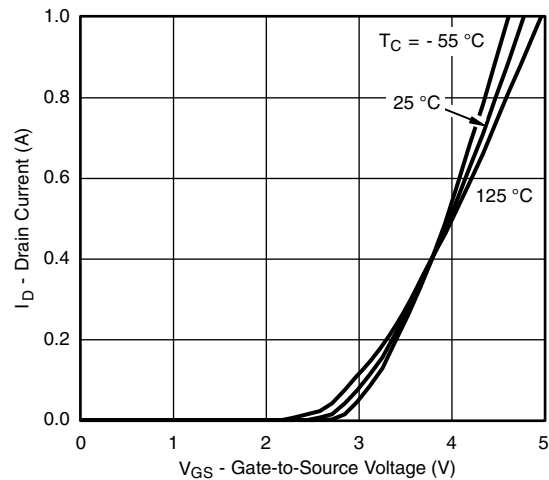
N-CHANNEL TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



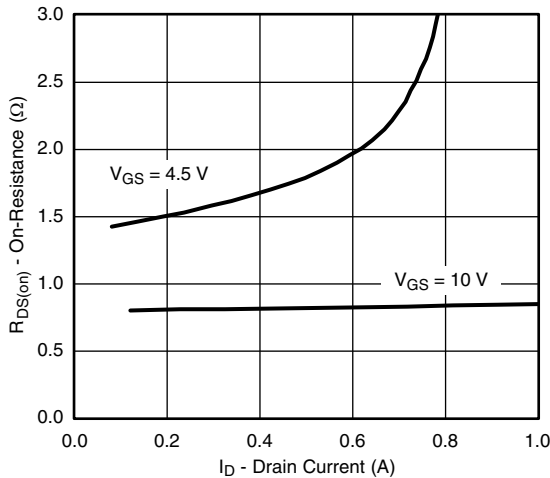
P-CHANNEL TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



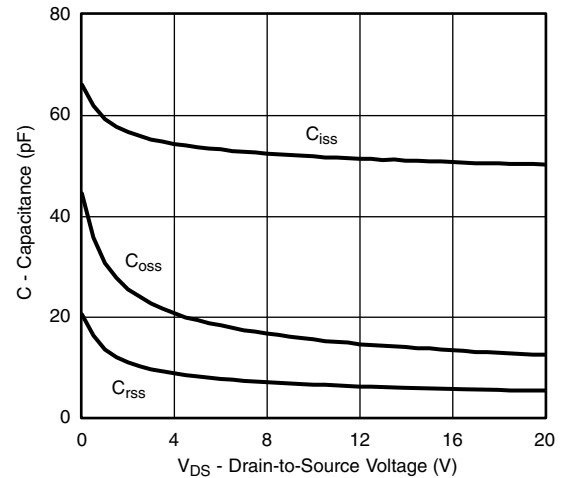
Output Characteristics



Transfer Characteristics

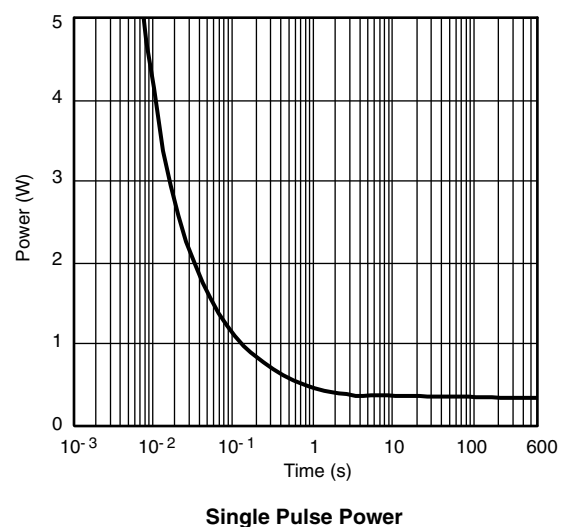
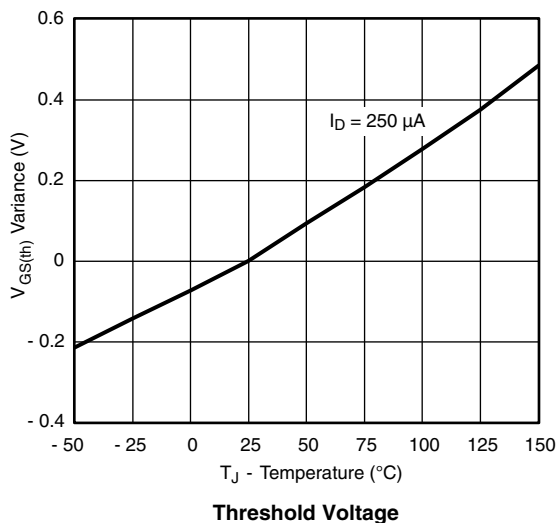
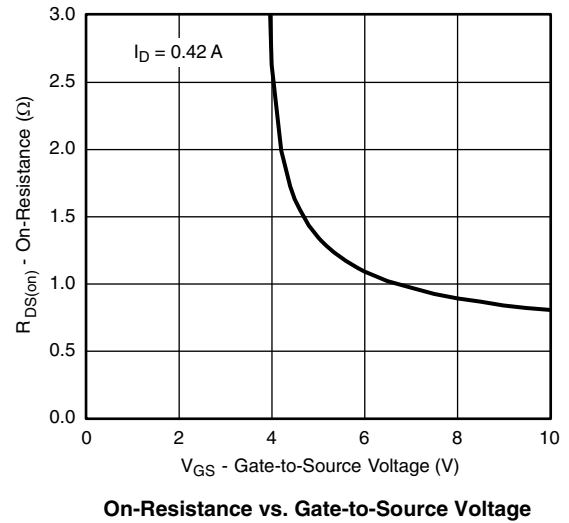
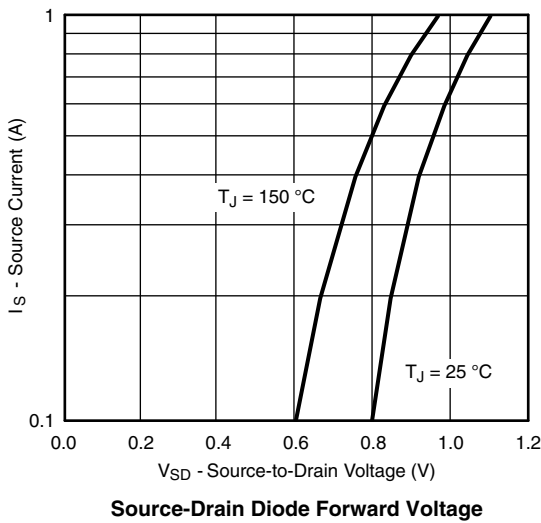
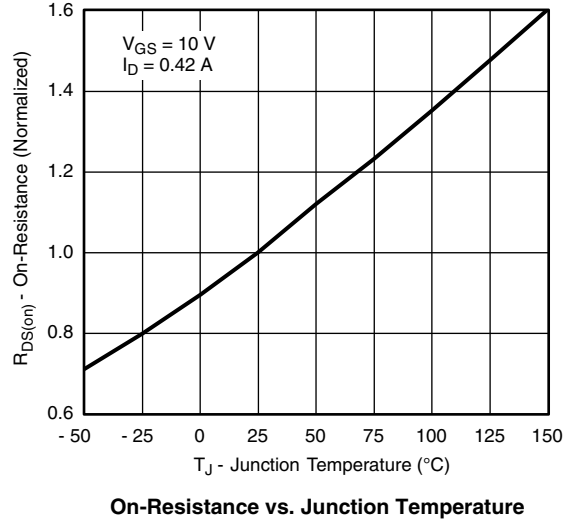
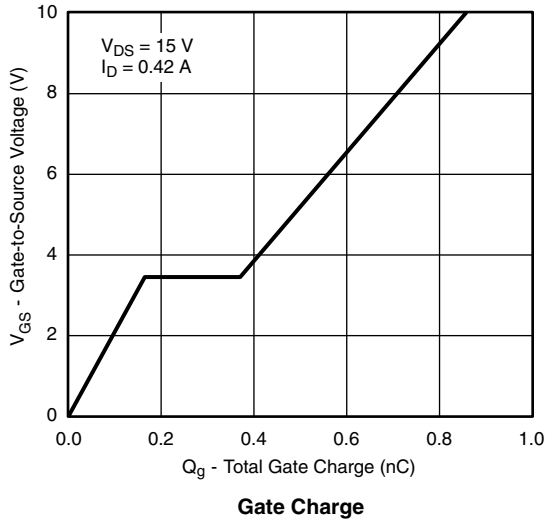


On-Resistance vs. Drain Current

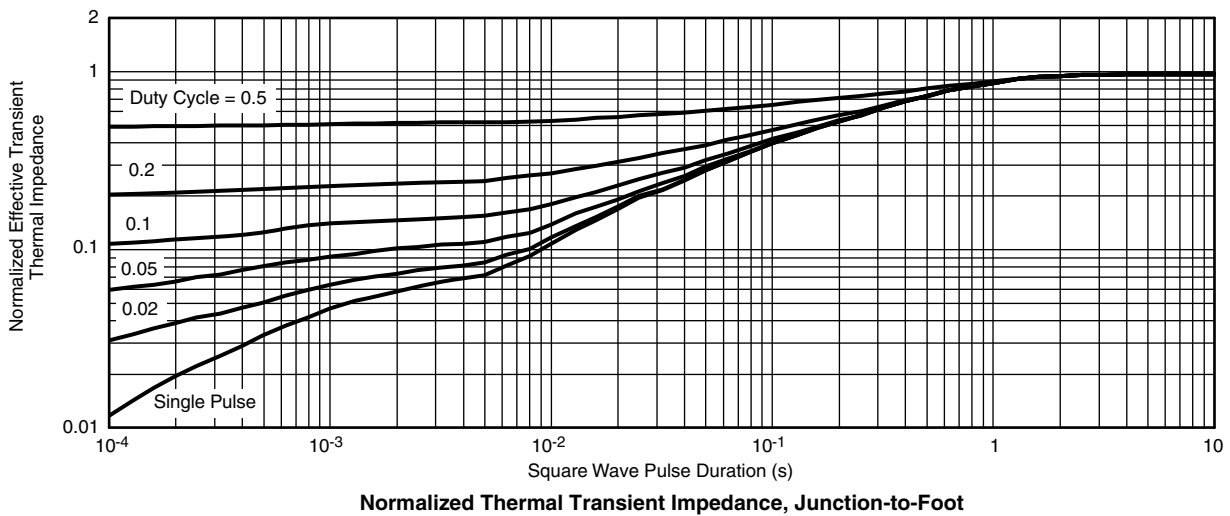
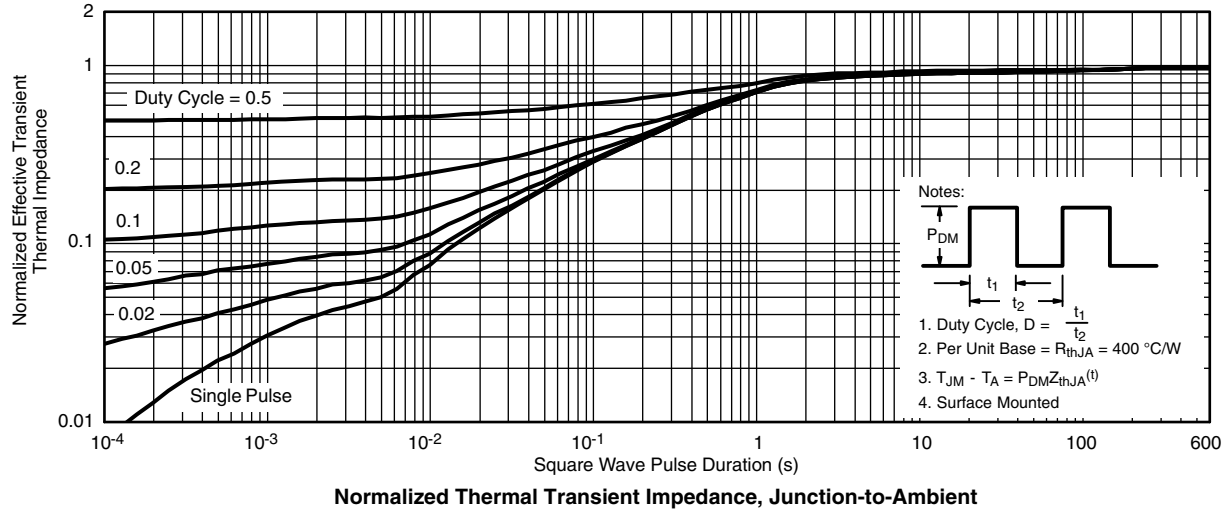


Capacitance

P-CHANNEL TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



P-CHANNEL TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



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